

Silicon NPN Power Transistors

2SC3795B

DESCRIPTION

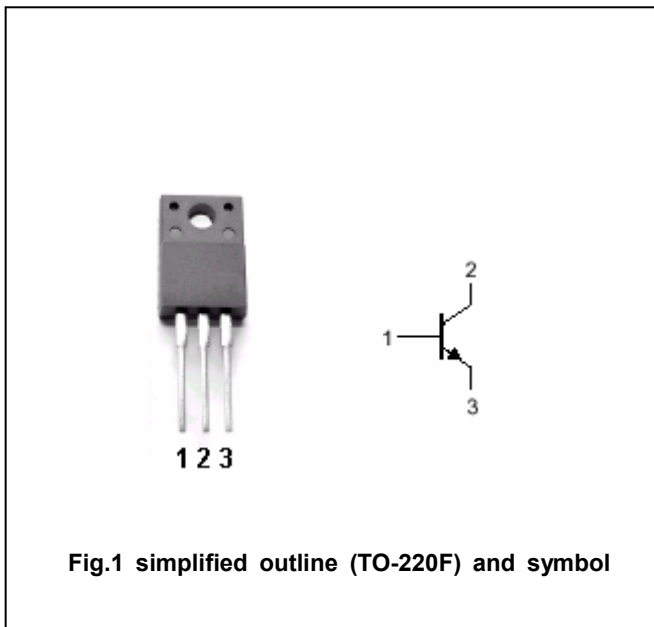
- With TO-220F package
- High breakdown voltage
- Fast switching speed
- Low collector saturation voltage

APPLICATIONS

- For high voltage ,high-speed switching applications

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |



Absolute maximum ratings (Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|---------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 1300 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 600 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 8 | V |
| I _C | Collector current | | 6 | A |
| I _B | Base current | | 3 | A |
| P _C | Collector dissipation | T _a =25°C | 2 | W |
| | | T _C =25°C | 50 | |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -55~150 | °C |

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-emitter sustaining voltage | I _C =0.2A , L=25mH | 600 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =3A; I _B =0.6A | | | 1.0 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =3A ; I _B =0.6A | | | 1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =800V; I _E =0 | | | 100 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =5V; I _C =0 | | | 100 | μA |
| h _{FE-1} | DC current gain | I _C =0.1A ; V _{CE} =5V | 15 | | | |
| h _{FE-2} | DC current gain | I _C =3A ; V _{CE} =5V | 8 | | | |
| f _T | Transition frequency | I _C =0.5A ; V _{CE} =10V | | 8 | | MHz |

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PACKAGE OUTLINE

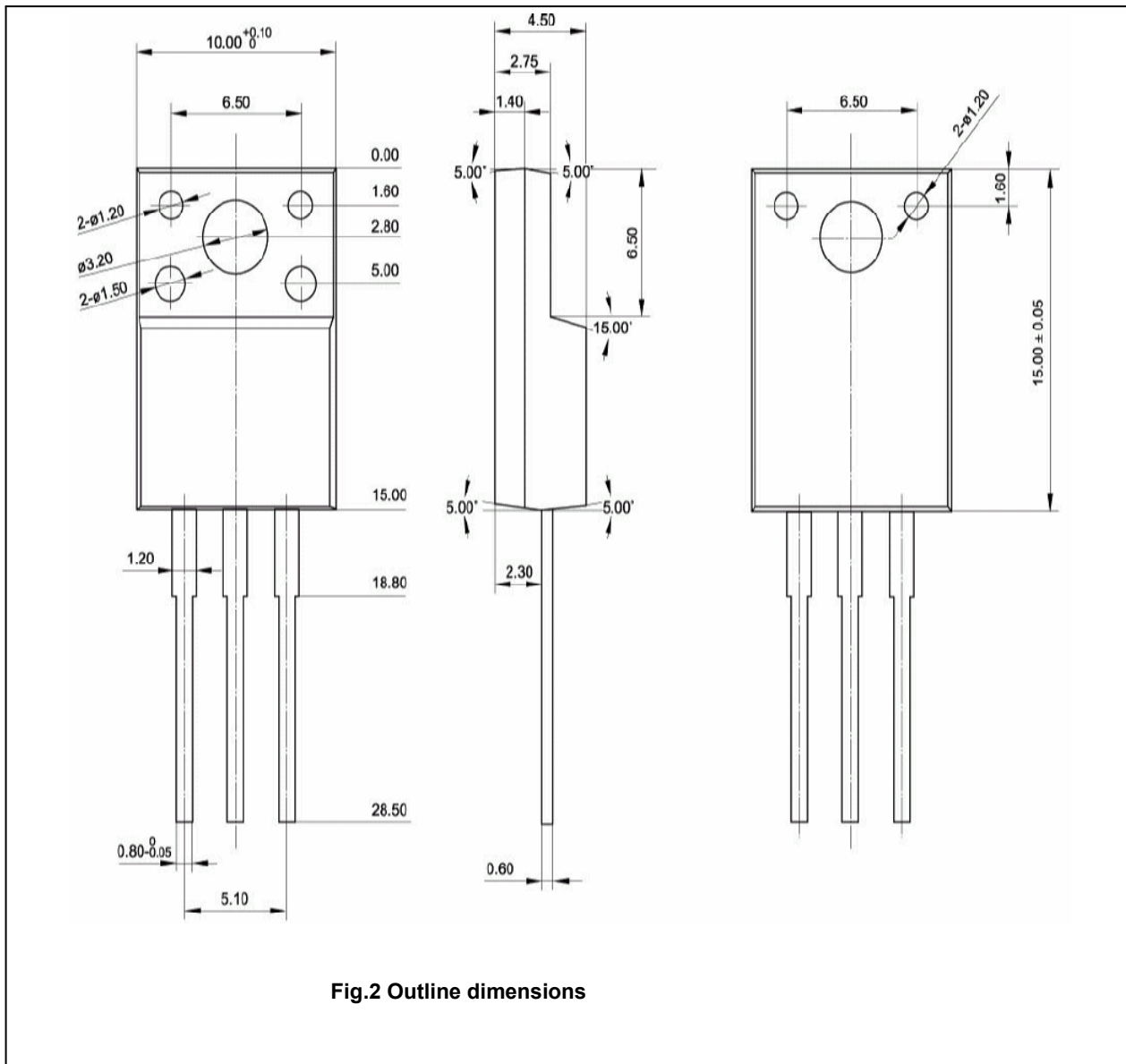


Fig.2 Outline dimensions